AMENDMENTS TO THE CLAIMS

Please **AMEND** claims 1, 9, 10 and 12 as shown below.

The following is a complete list of all claims in this application.

1. (Currently Amended) A thin film transistor liquid crystal device (TFT LCD), comprising:

a substrate;

a thin film transistor formed on said substrate~~,~~ and having a source electrode and a drain electrode, wherein the drain electrode is formed of multiple layers comprising an uppermost layer formed of Cr or MoW;

an insulating layer formed over said thin film transistor and having a contact hole exposing a portion of the drain electrode; and

a pixel electrode ~~provided corresponding to the thin film transistor,~~ formed on said insulating layer, and connected to the drain electrode through the contact hole, wherein the pixel electrode is formed of multiple layers comprising ~~wherein said pixel electrode is a multi-layered conductive layer and comprises~~ a lower layer formed of the same material as the uppermost layer of the ~~multiple layers,~~ drain electrode and an upper layer formed of ~~Al-containing~~ metal containing Al.

2-3. (Previously Cancelled)

4. (Previously Amended) The TFT LCD according to claim 1, wherein the pixel electrode further comprises an intermediate layer formed between the upper layer and the lower layer and formed of a material having an electro-negativity that is between that of the lower layer and that of the upper layer.

5. (Previously Amended) The TFT LCD according to claim 1, wherein the multiple layers further comprises a lower layer formed of MoW and an intermediate metal layer containing Al.

6. (Previously Amended) The TFT LCD according to claim 1, wherein said thin film transistor is a top-gate type polysilicon thin film transistor.

7. (Previously Amended) The TFT LCD according to claim 1, wherein said insulating layer is formed of a photo-sensitive organic insulating layer.

8. (Previously Amended) The TFT LCD according to claim 1, further comprising a plurality of small projections formed on an upper surface of said insulating layer and works as micro lens.

9. (Currently Amended) A thin film transistor liquid crystal device (TFT LCD), comprising:

a substrate;

a thin film transistor formed on said substrate~~,~~ and having a source electrode and a drain electrode, wherein the drain electrode is formed of Cr or MoW;

an insulating layer formed over said thin film transistor~~,~~ and having a contact hole exposing a portion of the drain electrode; and

a pixel electrode ~~provided corresponding to the thin film transistor,~~ formed on said insulating layer and connected to the drain electrode through the contact hole,

wherein said pixel electrode is ~~a~~ multi-layered ~~conductive layer and comprises~~ and comprises a lower layer formed of the same material as the drain electrode.

10. (Currently Amended) The TFT LCD of claim 9, wherein the pixel electrode further comprises an upper layer formed of metal containing Al.

11. (Previously Added) The TFT of claim 9, wherein the pixel electrode further comprises an intermediate layer formed between the upper layer and the lower layer and formed of a material having an electro-negativity that is between that of the lower layer and that of the upper layer.

12. (Currently Amended) The TFT LCD according to claim 9, wherein the drain electrode is multi-layered and ~~further~~ comprises an upper formed of Cr or MoW, a lower layer formed of MoW and an intermediate metal layer containing Al.

13. (Previously Added) The TFT LCD according to claim 9, wherein said thin film transistor is a top-gate type polysilicon thin film transistor.

14. (Previously Added) The TFT LCD according to claim 9, wherein said insulating layer is formed of a photo-sensitive organic insulating layer.

15. (Previously Added) The TFT LCD according to claim 9, further comprising a plurality of small projections formed on an upper surface of said insulating layer and works as micro lens.